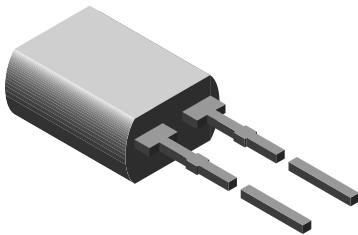


BPW46

Vishay Semiconductors



Silicon PIN Photodiode, RoHS Compliant



94 8632

DESCRIPTION

BPW46 is a PIN photodiode with high speed and high radiant sensitivity in a clear, side view plastic package. It is sensitive to visible and near infrared radiation.

FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 5 x 3 x 6.4
- Radiant sensitive area (in mm²): 7.5
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- High speed photo detector

PRODUCT SUMMARY			
COMPONENT	I_{ra} (mA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW46	50	± 65	430 to 1100

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW46	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5\text{ s}$	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	350	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 100 \mu A, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 V, E = 0$	I_{ro}		2	30	nA
Diode capacitance	$V_R = 0 V, f = 1 MHz, E = 0$	C_D		70		pF
	$V_R = 3 V, f = 1 MHz, E = 0$	C_D		25	40	pF
Open circuit voltage	$E_e = 1 mW/cm^2, \lambda = 950 nm$	V_o		350		mV
Temperature coefficient of V_o	$E_e = 1 mW/cm^2, \lambda = 950 nm$	TK_{V_o}		-2.6		mV/K
Short circuit current	$E_A = 1 klx$	I_k		70		μA
	$E_e = 1 mW/cm^2, \lambda = 950 nm$	I_k		47		μA
Temperature coefficient of V_k	$E_e = 1 mW/cm^2, \lambda = 950 nm$	TK_{V_k}		0.1		%/K
Reverse light current	$E_A = 1 klx, V_R = 5 V$	I_{ra}		75		μA
	$E_e = 1 mW/cm^2, \lambda = 950 nm, V_R = 5 V$	I_{ra}	40	50		μA
Angle of half sensitivity		ϕ		± 65		deg
Wavelength of peak sensitivity		λ_p		900		nm
Range of spectral bandwidth		$\lambda_{0.1}$		430 to 1100		nm
Noise equivalent power	$V_R = 10 V, \lambda = 950 nm$	NEP		4×10^{-14}		W/ \sqrt{Hz}
Rise time	$V_R = 10 V, R_L = 1 k\Omega, \lambda = 820 nm$	t_r		100		ns
Fall time	$V_R = 10 V, R_L = 1 k\Omega, \lambda = 820 nm$	t_f		100		ns

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

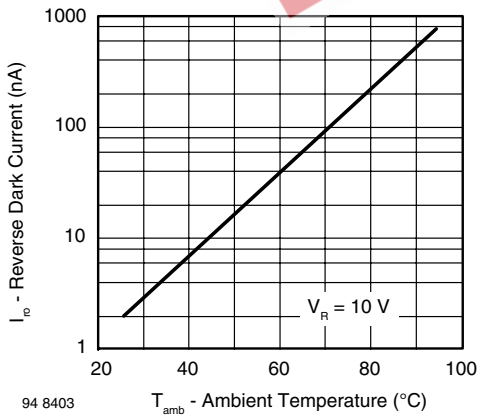


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

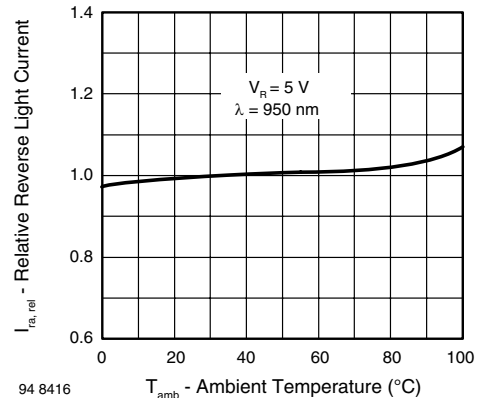


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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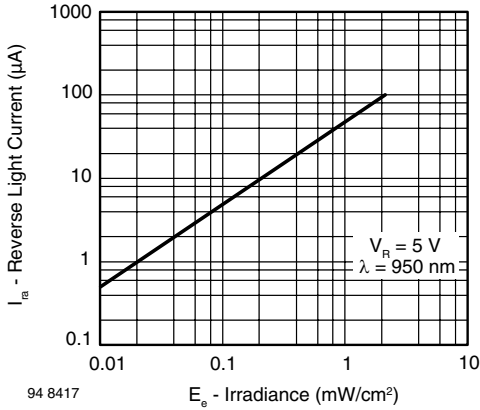


Fig. 3 - Reverse Light Current vs. Irradiance

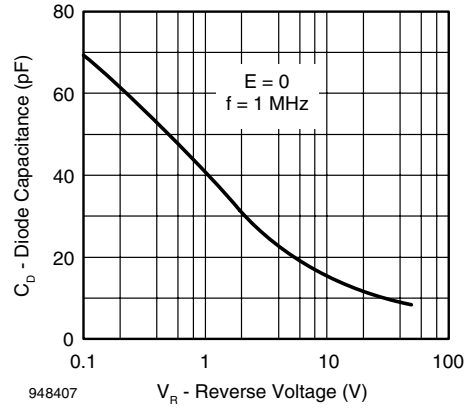


Fig. 6 - Diode Capacitance vs. Reverse Voltage

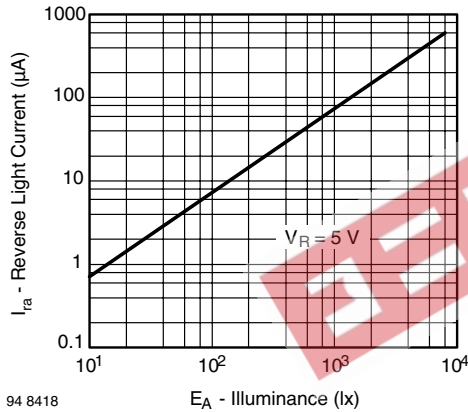


Fig. 4 - Reverse Light Current vs. Illuminance

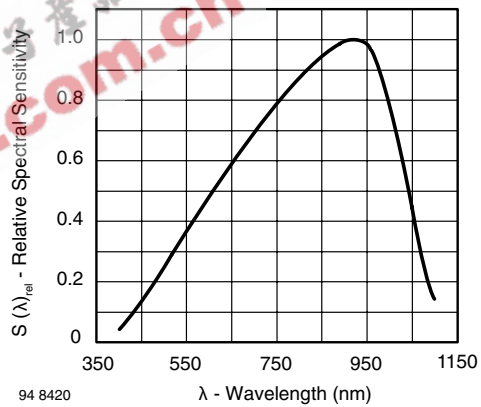


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

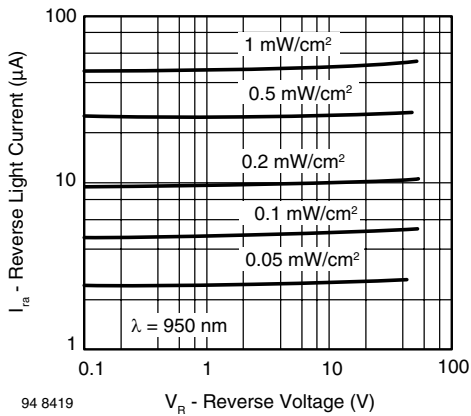


Fig. 5 - Reverse Light Current vs. Reverse Voltage

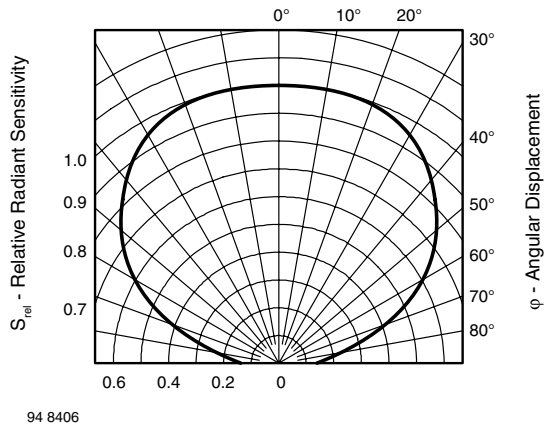
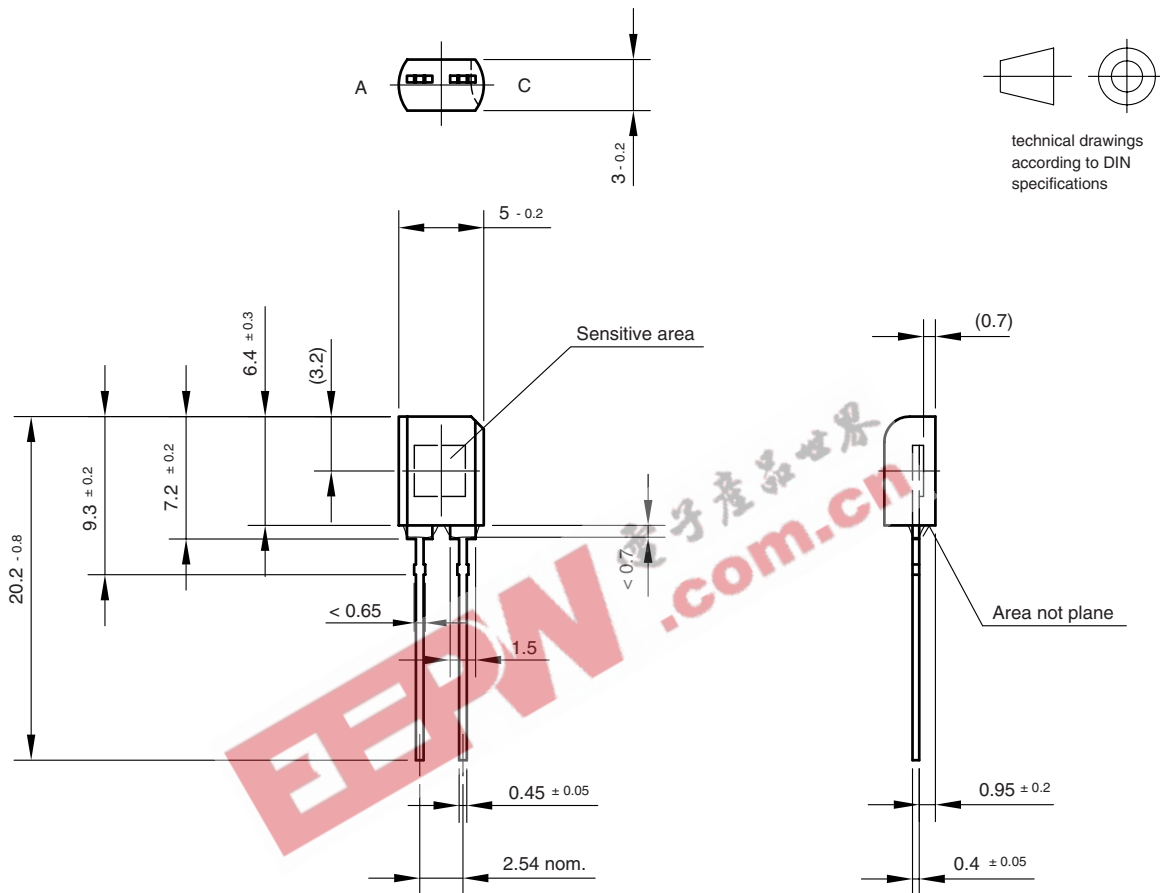


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5109.01-4
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